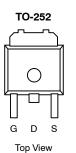


N-Channel 20-V (D-S) 175°C MOSFET

| PRODUCT SUMMARY | | | | |
|---------------------|----------------------------------|---------------------------------|--|--|
| V _{DS} (V) | r _{DS(on)} (Ω) | I _D (A) ^a | | |
| 20 | 0.005 @ V _{GS} = 10 V | 30 | | |
| | 0.0083 @ V _{GS} = 4.5 V | 23 | | |



Drain Connected to Tab

Order Number: SUD70N02-05P

FEATURES

- TrenchFET[®] Power MOSFET
- 175°C Junction Temperature
- PWM Optimized for High Efficiency
- 100% Rg Tested

APPLICATIONS

- Synchronous Buck DC/DC Conversion
 Desktop
 - Server

N-Channel MOSFET

S

D

| ABSOLUTE MAXIMUM RATINGS (T _A = 25° C UNLESS OTHERWISE NOTED) | | | | | |
|---|-----------------------|-----------------------------------|------------------|------------|--|
| Parameter | | Symbol | Limit | Unit | |
| Drain-Source Voltage | | V _{DS} | 20 | v | |
| Gate-Source Voltage | | V _{GS} | ±20 | | |
| | $T_A = 25^{\circ}C$ | | 30□ | | |
| Continuous Drain Current ^a | T _C = 25°C | | 70 ^b | - . | |
| Pulsed Drain Current | | I _{DM} | 100 | - ^ | |
| Continuous Source Current (Diode Conduction) ^a | | Is | 30 | | |
| | $T_A = 25^{\circ}C$ | | 7.5 ^a | | |
| Maximum Power Dissipation | $T_{C} = 25^{\circ}C$ | P _D | 65 | w | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to 175 | °C | |

G **O**

| THERMAL RESISTANCE RATINGS | | | | | | |
|--|------------------------|-------------------|---------|---------|------|--|
| Parameter | | Symbol | Typical | Maximum | Unit | |
| | $t \le 10 \text{ sec}$ | R _{thJA} | 16 | 20 | °C/W | |
| Maximum Junction-to-Ambient ^a | Steady State | | 40 | 50 | | |
| Maximum Junction-to-Case | | R _{thJC} | 1.9 | 2.3 | | |

Notes

- a. Surface Mounted on FR4 Board, t \leq 10 sec.
- b. Limited by package

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| SPECIFICATIONS (T _J = 25° C UNLESS OTHERWISE NOTED) | | | | | | | |
|---|----------------------|--|-----|------------------|--------|------|--|
| Parameter | Symbol | Test Condition | Min | Typ ^a | Max | Unit | |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V _{(BR)DSS} | V_{GS} = 0 V, I_D = 250 μ A | 20 | | | v | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$ | 0.8 | | 3.0 | | |
| Gate-Body Leakage | I _{GSS} | V_{DS} = 0 V, V_{GS} = ±20 V | | | ±100 | nA | |
| | | $V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | μΑ | |
| Zero Gate Voltage Drain Current | IDSS | V_{DS} = 16 V, V_{GS} = 0 V, T_{J} = 125°C | | | 50 | | |
| On-State Drain Current ^b | I _{D(on)} | $V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 50 | | | Α | |
| | | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | | 0.0041 | 0.005 | | |
| Drain-Source On-State Resistance ^b | r _{DS(on)} | V_{GS} = 10 V, I _D = 20 A, T _J = 125°C | | | 0.007 | Ω | |
| | | $V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | | 0.0064 | 0.0083 | | |
| Forward Transconductanceb | 9 _{fs} | $V_{DS} = 15 \text{ V}, \text{ I}_{D} = 20 \text{ A}$ | 15 | | | S | |
| Dynamic ^a | · · | | | | | | |
| Input Capacitance | C _{iss} | | | 2550 | | | |
| Output Capacitance | C _{oss} | V_{GS} = 0 V, V_{DS} = 10 V, f = 1 MHz | | 900 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | 415 | | | |
| Total Gate Charge ^c | Qg | | | 19 | 30 | nC | |
| Gate-Source Charge ^c | Q _{gs} | V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 50 A | | 7.5 | | | |
| Gate-Drain Charge ^c | Q _{gd} | | | 6.0 | | | |
| Gate Resistance | Rg | | 0.5 | 1.5 | 2.8 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | 11 | 20 | - ns | |
| Rise Time ^c | tr | V_{DD} = 10 V, R _L = 0.2 Ω | | 10 | 15 | | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_G = 2.5 \Omega$ | | 24 | 35 | | |
| Fall Time ^c | t _f | | | 9 | 15 | 1 | |
| Source-Drain Diode Ratings and | l Characteristi | c (T _C = 25°C) | • | • | • | | |
| Pulsed Current | I _{SM} | | | | 100 | А | |
| Diode Forward Voltage ^b | V _{SD} | $I_{F} = 50 \text{ A}, V_{GS} = 0 \text{ V}$ | | 1.2 | 1.5 | V | |
| Source-Drain Reverse Recovery Time | t _{rr} | I _F = 50 A, di/dt = 100 A/μs | 1 | 35 | 70 | ns | |

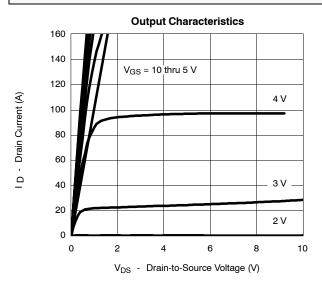
Notes

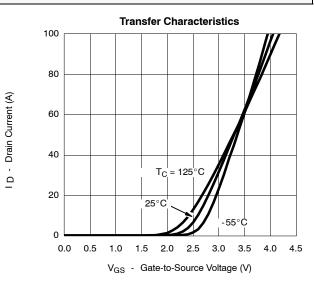
Guaranteed by design, not subject to production testing. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2%. a.

b.

c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



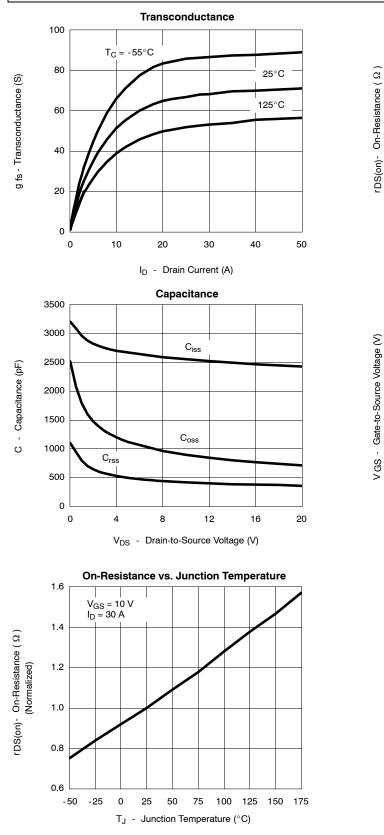


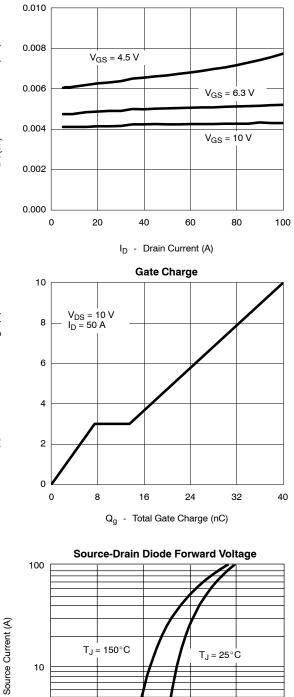


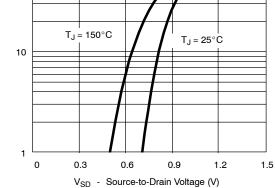
SUD70N02-05P Vishay Siliconix

On-Resistance vs. Drain Current

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



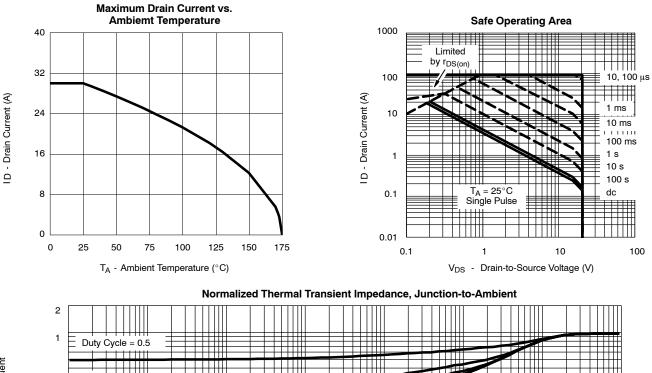


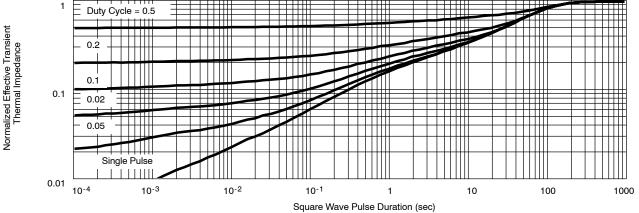


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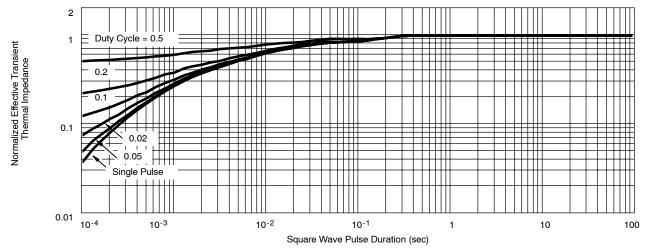
Vishay Siliconix

THERMAL RATINGS





Normalized Thermal Transient Impedance, Junction-to-Case





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